

## SILICON POWER TRANSISTOR 2SA1008

### PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1008 is a mold power transistor developed for high-speed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

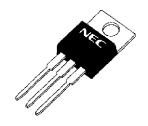
#### ORDERING INFORMATION

Part No.	Package		
2SA1008	TO-220AB		

#### **FEATURES**

- · Low collector saturation voltage
- · Fast switching speed
- Complementary transistor: 2SC2331

#### (TO-220AB)



#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-100	٧
Collector to emitter voltage	VCEO		-100	٧
Emitter to base voltage	VEBO		-7.0	٧
Collector current (DC)	Ic(DC)		-2.0	Α
Collector current (pulse)	IC(pulse)	PW ≤ 300 <i>μ</i> s,	-4.0	Α
		duty cycle ≤ 10%		
Base current (DC)	I <sub>B(DC)</sub>		-1.0	Α
Total power dissipation	Р⊤	Tc = 25°C	15	W
		T <sub>A</sub> = 25°C	1.5	W
Junction temperature	Tj		150	°C
Storage temperature	T <sub>stg</sub>		-55 to +150	°C

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#### ELECTRICAL CHARACTERISTICS (TA = 25°C)

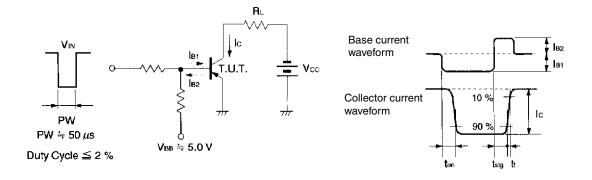
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	$Ic = -1.0 \text{ A}, I_{B1} = -0.1 \text{ A}, L = 1 \text{ mH}$	-100			V
Collector to emitter voltage	VCEX(SUS)1	Ic = $-1.0$ A, I <sub>B1</sub> = $-I_{B2}$ = $-0.1$ A, V <sub>BE(OFF)</sub> = $5.0$ V, L = $180$ $\mu$ H, clamped	-100			V
Collector to emitter voltage	VCEX(SUS)2	lc = -2.0 A, lb1 = -0.2 A, lb2 = 0.1 A, VBE(OFF) = 5.0 V, L = 180 $\mu$ H, clamped	-100			V
Collector cutoff current	Ісво	$V_{CB} = -100 \text{ V}, I_E = 0 \text{ A}$			-10	μΑ
Collector cutoff current	ICER	$V_{CE} = -100 \text{ V}, \text{ Rbe} = 51 \Omega, \text{ Ta} = 125^{\circ}\text{C}$			-1.0	mA
Collector cutoff current	ICEX1	$V_{CE} = -100 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V}$			-10	μΑ
Collector cutoff current	ICEX2	$V_{CE} = -100 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V},$ $T_A = 125^{\circ}\text{C}$			-1.0	mA
Emitter cutoff current	ІЕВО	V <sub>EB</sub> = -5.0 V, I <sub>C</sub> = 0 A			-10	μΑ
DC current gain	h <sub>FE1</sub>	$V_{CE} = -5.0 \text{ V, } I_{C} = -0.1 \text{ A}^{Note}$	40			
DC current gain	h <sub>FE2</sub>	$V_{CE} = -5.0 \text{ V, Ic} = -1.0 \text{ A}^{Note}$	40		200	
Collector saturation voltage	V <sub>CE(sat)</sub>	$I_C = -1.0 \text{ A}, I_B = -0.1 \text{ A}^{Note}$			-0.6	V
Base saturation voltage	V <sub>BE(sat)</sub>	$I_{C} = -1.0 \text{ A}, I_{B} = -0.1 \text{ A}^{Note}$			-1.5	V
Turn-on time	ton	Ic = $-1.0$ A, R <sub>L</sub> = $50$ Ω,			0.5	μs
Storage time	<b>t</b> stg	$I_{B1} = -I_{B2} = -0.1 \text{ A}, \text{ Vcc} \cong -50 \text{ V}$			1.5	μs
Fall time	tf	Refer to the test circuit.			0.5	μs

**Note** Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

#### **hfe CLASSIFICATION**

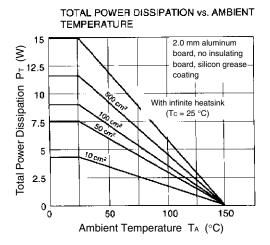
Marking	М	L	К	
h <sub>FE2</sub>	40 to 80	60 to 120	100 to 200	

#### SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



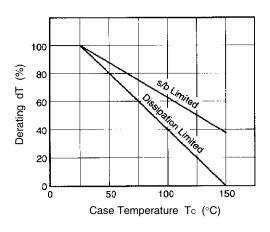


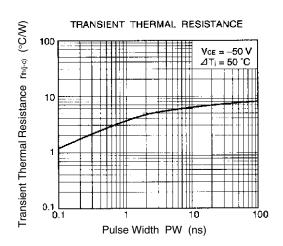
#### TYPICAL CHARACTERISTICS (TA = 25°C)



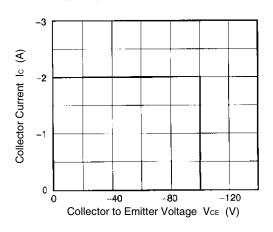
# FORWARD BIAS SAFE OPERATING AREA OPERATING AR

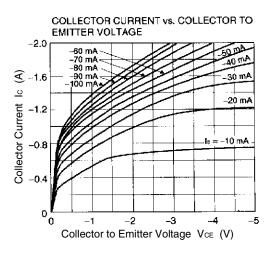
#### DERATING CURVE OF SAFE OPERATING AREA



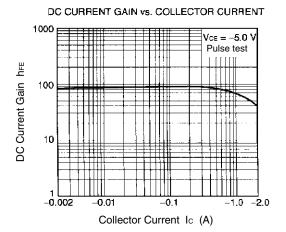


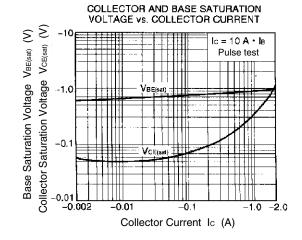
#### REVERSE BIAS SAFE OPERATING AREA

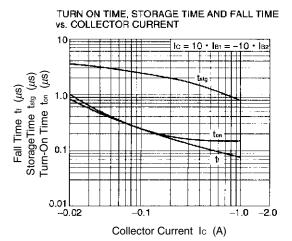




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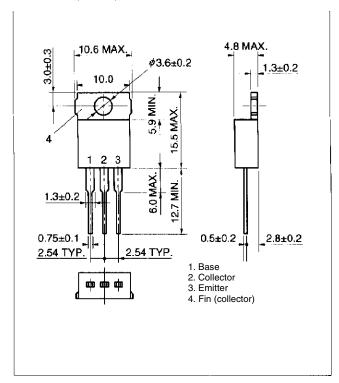






#### PACKAGE DRAWING (UNIT: mm)

TO-220AB (MP-25)



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